Abstracts

A modified cascode type low noise amplifier using dual common source transistors

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A Low Noise Amplifier (LNA) based on a GaAs MESFET has been implemented with a modified cascode configuration using two common source transistors to achieve high gain and linearity, low noise figure and low power consumption. The circuit design concept is introduced and implemented. The measured performance of the LNA at 900 MHz includes a gain of 17 dB, noise figure of 1.6 dB, and IIP3 of 8.5 dBm using a supply of 4.7 mA and 2.7 V.

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